EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	695	etch$3 same (without abscense "no" exclud$3) near2 (oxygen "O. sub.2" O2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 15:52
S2	10	(etch$3 same (without abscense "no" exclud$3) near2 (oxygen "O. sub.2" O2)) same (BCB Silk Flare polysiloxane siloxane (si silicon) near organic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:19
S3	17	(etch$3 same (without abscense "no" exclud$3) near2 (oxygen "O. sub.2" O2) same (silsesquioxane HSQ orthosilicate TEOS silane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:50
S4	102	etch$3 same (absence absent exclusion) near2 (oxygen "O. sub.2" O2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:50

S5	5	(etch$3 same (absence absent exclusion) near2 (oxygen "O. sub.2" O2) same (silsesquioxane HSQ orthosilicate TEOS silane BCB Silk Flare polysiloxane siloxane (si silicon) near organic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:54
S6	24	(etch$3 same (absence absent exclusion) near2 (oxygen "O. sub.2" O2)) and (silsesquioxane HSQ orthosilicate TEOS silane BCB Silk Flare polysiloxane siloxane (si silicon) near organic) not ((etch$3 same (absence absent exclusion) near2 (oxygen "O.sub.2" O2) same (silsesquioxane HSQ orthosilicate TEOS silane BCB Silk Flare polysiloxane siloxane (si silicon) near organic))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:54
S7	1334	etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 16:40

S8	13	(etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) near2 (oxygen "O. sub.2" O2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 16:38
S9	18	(etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) with (oxygen "O. sub.2" O2)) not ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 16:35

| S10 | 252 | (etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) and ((absence absent free without "no" exclu$4) with (oxygen "O. sub.2" O2)) not (((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2))) ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) with (oxygen "O. sub.2" O2)) not ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2003/11/12 14:17 |

		$4) near2 (oxygen "O.sub.2" O2))))				
S11	459	(etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) and ((absence absent free without "no" exclu$4) same (oxygen "O.sub.2" O2)) not (((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2))) ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) with (oxygen "O.sub.2" O2)) not ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/19 17:40

nitrogen)) same ((absence
absent free without "no" exclu
$4) near2 (oxygen "O.sub.2"
O2)))))

| S12 | 93 | (etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) and ((absence absent free without "no" exclu$4) near2 (oxygen "O.sub.2" O2)) not (((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) near2 (oxygen "O.sub.2" O2))) ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) with (oxygen "O.sub.2" O2)) not ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2003/05/22 16:40 |

		orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2))))				
S13	39	etch$3 with (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen) and ((absen$2 free without "no" exclu $4) near2 (oxygen "O.sub.2" O2)) not (((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2))) ((etch$3 same (low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu$4) with (oxygen "O.sub.2" O2)) not ((etch$3 same	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 16:46

		(low-k "low k" BCB Silk Flare polysiloxane silsesquioxane HSQ orthosilicate TEOS silane siloxane (si silicon) near (polymer organic)) same (N2 "N.sub.2" nitrogen)) same ((absence absent free without "no" exclu $4) near2 (oxygen "O.sub.2" O2)))))				
S14	0	(tetraethylorthosilane teos) near polysiloxane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:11
S15	30	(tetraethylorthosilane teos) with polysiloxane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:18
S16	95	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass) with polysiloxane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:11
S17	14	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass) near polysiloxane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/12 14:19

S18	2	(tetraethylorthosilane teos) near4 polysiloxane	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:15
S19	0	(tetraethylorthosilane teos) near6 polysiloxane not ((tetraethylorthosilane teos) near4 polysiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:15
S20	8	(tetraethylorthosilane teos) near10 polysiloxane not ((tetraethylorthosilane teos) near4 polysiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:19
S21	12	(tetraethylorthosilane teos) near20 polysiloxane not (((tetraethylorthosilane teos) near4 polysiloxane) ((tetraethylorthosilane teos) near10 polysiloxane not ((tetraethylorthosilane teos) near4 polysiloxane)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:22

S22	11	(tetraethylorthosilane teos) with polysiloxane not (((tetraethylorthosilane teos) near4 polysiloxane) ((tetraethylorthosilane teos) near10 polysiloxane not ((tetraethylorthosilane teos) near4 polysiloxane)) ((tetraethylorthosilane teos) near20 polysiloxane not (((tetraethylorthosilane teos) near4 polysiloxane) ((tetraethylorthosilane teos) near10 polysiloxane not ((tetraethylorthosilane teos) near4 polysiloxane)))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:26
S23	14	(tetraethylorthosilane teos) near dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/19 03:26
S24	271	(contact adj hole via) with temperature near (profile gradient variation chang$3) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 17:55
S25	39	(contact adj hole via) near2 temperature near2 (profile gradient variation chang$3) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:14

S26	0	contact adj hole via) near2 temperature near2 ((top opening) and bottom) and etch $3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:15
S27	34584	contact adj hole via) and temperature and ((top opening) and bottom) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:16
S28	1020	contact adj hole via) same temperature same ((top opening) and bottom) and etch $3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:34
S29	58	contact adj hole via) with temperature with ((top opening) and bottom) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:16
S30	58	((contact adj hole via) with temperature with ((top opening) and bottom) and etch$3) not ((contact adj hole via) near2 temperature near2 (profile gradient variation chang$3) and etch$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/08 18:17

S31	159	(contact adj hole via) same temperature same ((top opening) and sidewall and bottom) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:34
S32	17	(contact adj hole via) same temperature with ((top opening) and sidewall and bottom) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/08 18:35
S33	3	(contact adj hole via) near2 temperature with ((top opening) and bottom) and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 10:21
S34	1	"20010026952").PN.	US-PGPUB; USOCR	OR	OFF	2003/05/22 11:17
S35	1	PCT/DE99/02927	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:25
S36	1	"198 43 624.6"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:19

S37	0	"1999DE-198 43 624"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:19
S38	0	"1999DE 198 43 624"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:19
S39	0	"198 43 624"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:20
S40	1727230	"198" "43" "624".pran.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:21
S41	0	"198 43 624".pran.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:21
S42	1	"198 43 624.6".pran.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:21

S43	0	"19843624".pran.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:21
S44	1	"PCT/DE99/02927"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:23
S45	1	"1999DE-198 43 624.6"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:24
S46	532	englehardt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:25
S47	0	englehardt near manfred	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:25
S48	2	englehardt and manfred	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:27

S49	128	engelhardt and manfred	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:00
S50	78	engelhardt near manfred	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:28
S51	9	(engelhardt near manfred) and integrated.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:36
S52	69	(engelhardt near manfred) not ((engelhardt near manfred) and integrated.ti.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 11:36
S53	6	engelhardt and PCT/DE99??????	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/22 12:01
S54	14	etch$3 with (contact adj hole via) with temperature with gradient profile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 12:45

S55	0	etch$3 with (contact adj hole via) with temperature near bottom and sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 18:55
S56	0	etch$3 with (contact adj hole via) with temperature near2 bottom and sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 18:55
S57	2	etch$3 with (contact adj hole via) with temperature near2 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:21
S58	5	etch$3 with (contact adj hole via) with temperature near4 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 18:58
S59	3	S58 not S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 18:58
S60	59	etch$3 with (contact adj hole via) with temperature with bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 18:58

S61	9	etch$3 with (contact adj hole via) with temperature near6 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:03
S62	4	S61 not S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:03
S63	17	etch$3 with (contact adj hole via) with temperature near8 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:05
S64	8	S63 not S61	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:03
S65	21	etch$3 with (contact adj hole via) with temperature near10 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:07
S66	4	S65 not S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:05

S67	39	etch$3 with (contact adj hole via) with temperature near15 bottom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:07
S68	18	S67 not S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:17
S69	20	S60 not S67	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:17
S70	1	etch$3 with (contact adj hole via) with temperature near2 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:21
S71	9	etch$3 with (contact adj hole via) with temperature near4 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:24
S72	8	S71 not S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:22

S73	13	etch$3 with (contact adj hole via) with temperature near6 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:25
S74	4	S73 not S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:25
S75	13	etch$3 with (contact adj hole via) with temperature near8 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:25
S76	16	etch$3 with (contact adj hole via) with temperature near10 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:26
S77	21	etch$3 with (contact adj hole via) with temperature near12 sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:26
S78	8	S77 not S75	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 19:26

S79	1152	(contact adj hole via) with temperature with (gradient profile)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 12:46
S80	721	(contact adj hole via) with temperature near (gradient profile)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 12:45
S81	93	S80 and etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 12:46
S82	25	contact adj hole with temperature with (gradient profile)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/24 12:46
S83	945	(N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") with etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 06:11
S84	882	(N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") with etch$3	US-PGPUB; USPAT	OR	ON	2005/10/19 17:43
S85	352	(N2 "N.sub.2" nitrogen) near2 (CF4 "CF.sub.4") with etch$3	US-PGPUB; USPAT	OR	ON	2005/10/19 17:43

S86	187	(N2 "N.sub.2" nitrogen) near (CF4 "CF.sub.4") with etch$3	US-PGPUB; USPAT	OR	ON	2005/10/19 17:43
S87	111	S86 and etch$3 near (oxide silicon SiO2 "SiO.sub.2" Si02 "Si0.sub.2")	US-PGPUB; USPAT	OR	ON	2005/10/19 18:01
S88	36	S86 same etch$3 near (oxide silicon SiO2 "SiO.sub.2" Si02 "Si0.sub.2")	US-PGPUB; USPAT	OR	ON	2005/10/19 17:45
S89	25	S86 with etch$3 near (oxide silicon SiO2 "SiO.sub.2" Si02 "Si0.sub.2")	US-PGPUB; USPAT	OR	ON	2005/10/19 17:45
S90	11	S88 not S89	US-PGPUB; USPAT	OR	ON	2005/10/19 17:57
S91	18	S87 and ratio with ((N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2005/10/19 18:06
S92	11	S86 and ratio with ((N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4")) not S91	US-PGPUB; USPAT	OR	ON	2005/10/19 18:12
S93	15	S85 and ratio with ((N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4")) not (S91 S92)	US-PGPUB; USPAT	OR	ON	2005/10/19 18:12
S94	63	(N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") with etch$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 20:37
S95	2	(N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") with etch$3 and (TEOS BCB polysiloxane)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 20:15

S96	8	polysiloxane with (SiO2 "SiO.sub.2" Si02 "SiO.sub.2" silicon adj $2oxide) same etch$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 20:33
S97	27	polysiloxane with (SiO2 "SiO.sub.2" Si02 "SiO.sub.2" silicon adj $2oxide) same etch$3	US-PGPUB; USPAT	OR	ON	2005/10/20 20:33
S98	17	(N2 "N.sub.2" nitrogen CF4 "CF.sub.4") and polysiloxane with (SiO2 "SiO.sub.2" Si02 "SiO.sub.2" silicon adj $2oxide) same etch$3	US-PGPUB; USPAT	OR	ON	2005/10/20 20:37
S99	8	(US-6060400-$ or US-6136211-$ or US-6143665-$ or US-6325861-$ or US-6355567-$).did. or (WO-9933096-$).did. or (JP-11145114-$).did. or (US-5854119-$).did.	USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/21 06:11
S100	8	S99 and ((N2 "N.sub.2" nitrogen) same (CF4 "CF.sub.4") same etch $3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 06:12
S101	5	plasma and ((N2 "N.sub.2" nitrogen) with (damag$3) near (interior chamber reactor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:09

S102	7025	plasma and ((N2 "N.sub.2" nitrogen) with (react$3 damag $3 with (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:10
S103	1638	plasma and ((N2 "N.sub.2" nitrogen) near3 (react$3 damag $3 near3 (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:10
S104	842	plasma and ((N2 "N.sub.2" nitrogen) near2 (react$3 damag $3 near2 (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:11
S105	189	plasma and ((N2 "N.sub.2" nitrogen) near (react$3 damag $3 near (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:11
S106	36	plasma same ((N2 "N.sub.2" nitrogen) near (react$3 damag $3 near (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:11
S107	28	plasma with ((N2 "N.sub.2" nitrogen) near (react$3 damag $3 near (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:11

S108	4	plasma near ((N2 "N.sub.2" nitrogen) near (react$3 damag $3) near (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:12
S109	12	plasma near3 ((N2 "N.sub.2" nitrogen) near (react$3 damag $3) near (component interior chamber reactor)) not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:13
S110	3	S109 not S108	US-PGPUB; USPAT	OR	ON	2005/10/21 17:17
S111	8	S107 not S109	US-PGPUB; USPAT	OR	ON	2005/10/21 17:16
S112	5	S106 not S107	US-PGPUB; USPAT	OR	ON	2005/10/21 17:16
S113	5	S109 not (S108 S110)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:18
S114	8	S107 not (S109 S111)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:20

S115	3	S106 not (S107 S112)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:20
S116	0	more adj (N2 "N.sub.2" nitrogen) near (CF4 "CF.sub.4") same etch $3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:54
S117	1	more adj (N2 "N.sub.2" nitrogen) near4 (CF4 "CF.sub.4") same etch $3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:54
S118	2	(greater more higher) near (N2 "N.sub.2" nitrogen) near4 (CF4 "CF.sub.4") same etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:55
S119	32	(greater more higher) near2 (N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") same etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 17:58
S120	23	ratio near2 (N2 "N.sub.2" nitrogen) near2 (CF4 "CF.sub.4") same etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 18:04

S121	2	flow adj ratio near4 (N2 "N. sub.2" nitrogen) near4 (CF4 "CF. sub.4") same etch$3 not S120	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 18:22
S122	1	flow adj ratio with (N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") same etch$3 not (S120 "22")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 18:23
S123	1	flow near ratio with (N2 "N. sub.2" nitrogen) with (CF4 "CF. sub.4") same etch$3 not (S120 "22")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 18:23
S124	13	ratio with (N2 "N.sub.2" nitrogen) with (CF4 "CF.sub.4") same etch$3 not (S120 "22")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 18:24
S125	1	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass) with polysiloxane with structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:12
S126	25	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass) with polysiloxane same structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:17

S127	9	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass) same polysiloxane same structure not S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:19
S128	1156	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) near structure not S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:19
S129	776	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) adj structure not S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:19
S130	10	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) adj chemical adj structure not S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:22
S131	10	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) near chemical adj structure not S126	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:22
S132	0	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) near chemical adj structure not (S126 S130)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:22

S133	93	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) with chemical adj structure not (S126 S130)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:22
S134	17	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) near4 chemical adj structure not (S126 S130)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:24
S135	11	(tetraethylorthosilane teos sog "spin-on-glass" spin near glass polysiloxane) near6 chemical adj structure not (S126 S130 S134)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:26
S136	65	S133 not (S126 S130 S134 S135)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:33
S137	4	polysiloxane adj (film layer) with (SiO2 "SiO.sub.2" SiO2 "SiO. sub.2" silicon adj $2oxide) with etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:35
S138	9	polysiloxane adj (film layer) with (SiO2 "SiO.sub.2" SiO2 "SiO. sub.2" silicon adj $2oxide) same etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 19:38

S139	1	("6284149").PN.	USPAT	OR	OFF	2006/03/24 12:35
S140	137	(etch$4 same (N2 "N.sub.2") with (CF4 "CF.sub.4")) and (etch $4 same (oxide SiO2 "SiO. sub.2")) and ((etch$4 adj stop$4 etchstop) with (oxide SiO2 "SiO. sub.2"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:44
S141	69	S140 and (silsesquioxane HSQ orthosilicate TEOS silane BCB Silk Flare polysiloxane siloxane (si silicon) near organic)	US-PGPUB; USPAT	OR	ON	2006/03/24 18:46
S142	8	S140 and BCB	US-PGPUB; USPAT	OR	ON	2006/03/24 14:37
S143	6	S140 and (Silk Flare)	US-PGPUB; USPAT	OR	ON	2006/03/24 14:43
S144	10	S140 and ((si silicon si-containing silicon-containing) near3 organic)	US-PGPUB; USPAT	OR	ON	2006/03/24 15:05
S145	52	S141 not (S142 S143 S144)	US-PGPUB; USPAT	OR	ON	2006/03/24 17:45
S146	118	(etch$4 with (N2 "N.sub.2") with (CF4 "CF.sub.4")) and (etch$4 with (oxide SiO2 "SiO.sub.2")) and ((etch$4 adj stop$4 etchstop) with (oxide SiO2 "SiO. sub.2"))	US-PGPUB; USPAT	OR	ON	2006/03/24 17:23

S147	51	(etch$4 with (N2 "N.sub.2") with (CF4 "CF.sub.4")) and (etch$4 with (oxide SiO2 "SiO.sub.2")) and ((etch$4 adj stop$4 etchstop) near3 (oxide SiO2 "SiO.sub.2"))	US-PGPUB; USPAT	OR	ON	2006/03/24 17:44
S148	31	S147 not S141	US-PGPUB; USPAT	OR	ON	2006/03/24 17:24
S149	36	S140 not (S141 S142 S143 S144 S147)	US-PGPUB; USPAT	OR	ON	2006/03/24 17:53
S150	34	S146 not (S141 S142 S143 S144 S147)	US-PGPUB; USPAT	OR	ON	2006/03/24 17:57
S151	0	S146 not (S140 S141 S142 S143 S144 S147)	US-PGPUB; USPAT	OR	ON	2006/03/24 17:53
S152	59	(etch$4 with (N2 "N.sub.2") near2 (CF4 "CF.sub.4")) and (etch$4 with (oxide SiO2 "SiO.sub.2")) and ((etch$4 adj stop$4 etchstop) with (oxide SiO2 "SiO.sub.2"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:45
S153	26	(etch$4 with (N2 "N.sub.2") near2 (CF4 "CF.sub.4")) and (etch$4 near3 (oxide SiO2 "SiO.sub.2")) and ((etch$4 adj stop$4 etchstop) near3 (oxide SiO2 "SiO.sub.2"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:45

S154	13	S153 and (coral hosp silsesquioxane HSQ orthosilicate TEOS silane BCB Silk Flare polysiloxane siloxane (si silicon) near organic)	US-PGPUB; USPAT	OR	ON	2006/03/24 18:51
S155	0	etch$3 with BCB with ((C4F8 "C. sub.4 F.sub.8") with (CF4 "CF. sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:52
S156	1	etch$4 same BCB same ((C4F8 "C.sub.4 F.sub.8") same (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:53
S157	51	etch$4 and BCB and ((C4F8 "C. sub.4 F.sub.8") same (CF4 "CF. sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:56
S158	1	etch$4 and BCB same ((C4F8 "C. sub.4 F.sub.8") same (CF4 "CF. sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:20
S159	45	etch$4 and BCB and ((C4F8 "C. sub.4 F.sub.8") with (CF4 "CF. sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 18:54
S160	0	etch$4 and ((C4F8 "C.sub.4 F. sub.8") with (CF4 "CF.sub.4")) same BCB	US-PGPUB; USPAT	OR	ON	2006/03/24 18:54
S161	44	etch$4 same ((C4F8 "C.sub.4 F. sub.8") with (CF4 "CF.sub.4")) and BCB	US-PGPUB; USPAT	OR	ON	2006/03/24 18:55
S162	0	etch$4 same ((C4F8 "C.sub.4 F. sub.8") with (CF4 "CF.sub.4")) same BCB	US-PGPUB; USPAT	OR	ON	2006/03/24 18:55

S163	26	etch$4 same ((C4F8 "C.sub.4 F. sub.8") near3 (CF4 "CF.sub.4")) and bcb	US-PGPUB; USPAT	OR	ON	2006/03/24 18:57
S164	39	etch$4 and BCB and ((C4F8 "C. sub.4 F.sub.8") same (CF4 "CF. sub.4")) and (N2 "N.sub.2")	US-PGPUB; USPAT	OR	ON	2006/03/24 18:56
S165	5	etch$4 same ((C4F8 "C.sub.4 F. sub.8") near3 (CF4 "CF.sub.4") same (N2 "N.sub.2")) and bcb	US-PGPUB; USPAT	OR	ON	2006/03/24 18:58
S166	34	S164 not S165	US-PGPUB; USPAT	OR	ON	2006/03/24 20:49
S167	21	S163 not S165	US-PGPUB; USPAT	OR	ON	2006/03/24 20:16
S168	43	bcb near dielectric adj constant	US-PGPUB; USPAT	OR	ON	2006/03/24 20:17
S169	43	bcb adj dielectric adj constant	US-PGPUB; USPAT	OR	ON	2006/03/24 20:17
S170	14	S166 not S167	US-PGPUB; USPAT	OR	ON	2006/03/24 21:01
S171	11	S157 not (S164 S166 S167 S170)	US-PGPUB; USPAT	OR	ON	2006/03/24 21:03
S172	0	etch$4 with (benzocyclobutene cyclotene BCB) and ethc$4 same ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:21
S173	7	etch$4 with (benzocyclobutene cyclotene BCB) and etch$4 same ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:24

S174	7	etch$4 with (benzocyclobutene cyclotene BCB) and ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S175	49	etch$4 and (benzocyclobutene cyclotene BCB) and ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S176	0	etch$4 and (benzocyclobutene cyclotene BCB) same ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S177	0	etch$4 same (benzocyclobutene cyclotene BCB) same ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S178	14	etch$4 same (benzocyclobutene cyclotene BCB) and ((C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4"))	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S179	0	S178 not S175	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S180	7	S178 not S174	US-PGPUB; USPAT	OR	ON	2006/03/24 21:25
S181	0	etch$4 with (polysiloxane BCB FLARE) with (C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4")	US-PGPUB; USPAT	OR	ON	2006/03/27 13:05
S182	0	etch$4 with (polysiloxane BCB FLARE) with (C4F8 "C.sub.4 F.sub.8") with (CF4 "CF.sub.4")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:05

S183	1	etch$4 same (polysiloxane BCB FLARE) same (C4F8 "C.sub.4 F.sub.8") same (CF4 "CF.sub.4")	US-PGPUB; USPAT	OR	ON	2006/03/27 13:06
S184	1	etch$4 same (polysiloxane BCB FLARE) same (C4F8 "C.sub.4 F.sub.8") same (CF4 "CF.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:06
S185	26	etch$4 same (polysiloxane BCB FLARE) and (C4F8 "C.sub.4 F.sub.8") same (CF4 "CF.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:39
S186	16	etch$4 with (polysiloxane BCB FLARE) and (C4F8 "C.sub.4 F.sub.8") same (CF4 "CF.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:19
S187	10	S185 not S186	US-PGPUB; USPAT	OR	ON	2006/03/27 13:19
S188	20	etch$4 same (polysiloxane BCB FLARE) same (CF4 "CF.sub.4") same (N2 "N.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:28
S189	54	etch$4 same (polysiloxane BCB FLARE) and etch$4 same (CF4 "CF.sub.4") same (N2 "N.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:37

S190	34	S189 not S188	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:28
S191	3	etch$4 same (polysiloxane BCB FLARE) and etch$4 same ($5fluoromethane) same (N2 "N. sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:38
S192	28	etch$4 same (polysiloxane BCB FLARE) and (C4F8 "C.sub.4 F. sub.8" perfluorocyclobutane octafluorocyclobutane perfluoro $3butene octafluoro$3butene) same (CF4 "CF.sub.4" perfluoromethane tetrafluoromethane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:49
S193	57	S192 not5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:42
S194	2	S192 not S185	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:43

S195	657	etch$4 same (C4F8 "C.sub.4 F. sub.8" perfluorocyclobutane octafluorocyclobutane perfluoro $3butene octafluoro$3butene) with (CF4 "CF.sub.4" perfluoromethane tetrafluoromethane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 13:50
S196	78	etch$4 same (C4F8 "C.sub.4 F. sub.8" perfluorocyclobutane octafluorocyclobutane perfluoro $3butene octafluoro$3butene) with (CF4 "CF.sub.4" perfluoromethane tetrafluoromethane) with (N2 "N. sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:17
S197	21	(US-6720249-$ or US-6472717-$ or US-6455411-$ or US-6440864- $ or US-6326307-$ or US-6284642-$ or US-6211051-$ or US-6180975-$ or US-6177329-$ or US-6163407-$ or US-6159661- $ or US-6143665-$ or US-6040223-$ or US-6033979-$ or US-6014979-$ or US-5990015-$ or US-5972789-$ or US-5801094- $ or US-5654233-$ or US-5038713-$).did. or (JP-11145114- $).did.	USPAT; JPO	OR	ON	2006/03/27 14:16

S198	21	S197 and (C4F8 "C.sub.4 F. sub.8" perfluorocyclobutane octafluorocyclobutane perfluoro $3butene octafluoro$3butene CF4 "CF.sub.4" perfluoromethane tetrafluoromethane N2 "N.sub.2" polysiloxane BCB FLARE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:28
S199	8	S198 and (polysiloxane BCB FLARE (((si silicon) adj containing) silicon-containing si-containing) near (low-k low adj dielectric) organic))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:33
S200	1	S198 and (polysiloxane BCB FLARE (((si silicon) adj containing) silicon-containing si-containing) near (low-k low adj dielectric) organic))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/27 14:33
S201	1	"6506680".PN.	USPAT	OR	OFF	2007/05/14 12:21
S202	1	S201 and select$6	US-PGPUB; USPAT	OR	ON	2007/05/14 12:22
S203	1570	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) and selectiv$6 and (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/10/10 08:25

S204	1026	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) and selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 12:35
S205	632	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) and selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 12:35
S206	522	etch$4 with (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) and selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 12:35
S207	98	etch$4 with (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 12:36
S208	53	S207 and organic	US-PGPUB; USPAT	OR	ON	2007/05/14 13:10
S209	98	etch$4 with (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 13:44
S210	53	S209 and organic	US-PGPUB; USPAT	OR	ON	2007/05/14 13:11

S211	45	S209 not S210	US-PGPUB; USPAT	OR	ON	2007/05/14 13:11
S212	115	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 13:50
S213	17	S212 not S209	US-PGPUB; USPAT	OR	ON	2007/05/14 13:44
S214	211	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 14:02
S215	96	S214 not S212	US-PGPUB; USPAT	OR	ON	2007/05/14 13:51
S216	18	S215 and etch$4 with organic	US-PGPUB; USPAT	OR	ON	2007/05/14 14:03
S217	1026	etch$4 same (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) and selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 14:02
S218	296	S217 not S214 and etch$4 with organic	US-PGPUB; USPAT	OR	ON	2007/05/14 14:03
S219	139	S217 not S214 and organic near (etch$4 dielectric ILD low-k)	US-PGPUB; USPAT	OR	ON	2007/05/14 14:07

S220	11	(US-20010010970-$).did. or (US-6143665-$ or US-6107155-$ or US-6316160-$ or US-6475918-$ or US-6309962-$ or US-6211061-$ or US-6570257-$ or US-6410437-$ or US-6319815-$ or US-6168726-$).did.	US-PGPUB; USPAT	OR	ON	2007/05/14 15:21
S221	211	etch$4 same (((C4F8 "C.sub.4 F.sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 15:21
S222	1026	etch$4 same (((C4F8 "C.sub.4 F.sub.8") (CF4 "CF.sub.4")) same (N2 "N.sub.2" nitrogen)) and selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 15:21
S223	139	S222 not S221 and organic near (etch$4 dielectric ILD low-k)	US-PGPUB; USPAT	OR	ON	2007/05/14 15:21
S224	8	S220 and S223	US-PGPUB; USPAT	OR	ON	2007/05/14 15:22
S225	3	S220 and S221	US-PGPUB; USPAT	OR	ON	2007/05/14 15:22
S226	11	S224 S225	US-PGPUB; USPAT	OR	ON	2007/05/14 15:27
S227	0	S226 and polysiloxane	US-PGPUB; USPAT	OR	ON	2007/05/14 15:28

S228	98	etch$4 with (((C4F8 "C.sub.4 F. sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/10/10 05:56
S229	53	S228 and organic	US-PGPUB; USPAT	OR	ON	2007/05/14 15:28
S230	5	S229 and polysiloxane	US-PGPUB; USPAT	OR	ON	2007/05/14 15:28
S231	16	(US-20060166485-$ or US-20010010970-$ or US-20010009803-$).did. or (US-6143665-$ or US-6107155-$ or US-6316160-$ or US-6475918-$ or US-7060605-$ or US-6909190-$ or US-6309962-$ or US-6211061-$ or US-6570257-$ or US-6410437-$ or US-6319815-$ or US-6316351-$ or US-6168726-$).did.	US-PGPUB; USPAT	OR	ON	2007/05/14 15:29
S232	4	(US-6326307-$ or US-6455411-$ or US-6872665-$ or US-6686296-$).did.	USPAT	OR	ON	2007/05/14 15:29

| S233 | 33 | (US-20020058362-$).did. or (US-6143665-$ or US-5801094-$ or US-6211051-$ or US-6342449-$ or US-6319815-$ or US-6284149-$ or US-6211035-$ or US-6326307-$ or US-6060400-$ or US-6440864-$ or US-6720249-$ or US-6177329-$ or US-6221745-$ or US-6284642-$ or US-6180975-$ or US-6015751-$ or US-5204276-$ or US-6737350-$ or US-6573196-$ or US-6472717-$ or US-6455411-$ or US-6159661-$ or US-6040223-$ or US-6033979-$ or US-5990015-$ or US-5972789-$).did. or (US-6180518-$ or US-6163407-$ or US-6014979-$ or US-5654233-$ or US-5038713-$).did. or (JP-11145114-$).did. | US-PGPUB; USPAT; JPO | OR | ON | 2007/05/14 15:29 |
| S234 | 10 | (US-20050090634-$).did. or (US-6143665-$ or US-6325861-$ or US-6136211-$ or US-6060400-$ or US-6355567-$ or US-4976818-$).did. or (WO-9933096-$).did. or (JP-11145114-$).did. or (US-5854119-$).did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2007/05/14 15:30 |

S235	24	(US-20020195419-$ or US-20020074309-$ or US-20010027016-$).did. or (US-5835987-$ or US-6461962-$ or US-6331380-$ or US-6168726-$ or US-6245489-$ or US-5604380-$ or US-6340435-$ or US-6281135-$ or US-6255180-$ or US-5658425-$ or US-5522957-$ or US-5173151-$ or US-6235453-$ or US-6417090-$ or US-6153514-$ or US-6472317-$ or US-5721156-$ or US-6051153-$ or US-5605600-$ or US-6376386-$ or US-6617253-$).did.	US-PGPUB; USPAT	OR	ON	2007/05/14 15:30
S236	3	(S231 S232 S233 S234 S235) and polysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:38
S237	5	S230 not S236	US-PGPUB; USPAT	OR	ON	2007/05/14 15:33
S238	115	etch$4 same (((C4F8 "C.sub.4 F.sub.8") (CF4 "CF.sub.4")) with (N2 "N.sub.2" nitrogen)) same selectiv$6 same (photoresist resist)	US-PGPUB; USPAT	OR	ON	2007/05/14 15:38

S239	5	S238 and polysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:40
S240	0	S239 not S230	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:39
S241	5	S221 and polysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:40
S242	296	S222 not S221 and etch$4 with organic	US-PGPUB; USPAT	OR	ON	2007/05/14 15:40
S243	13	S242 and polysiloxane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:40

S244	13	S243 not (S236 S237)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/14 15:41
S245	2	("6352931").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/14 16:51
S246	1	etch$4 with polysiloxane with ((CF4 "CF.sub.4") with (N2 "N. sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 09:33
S247	6	etch$4 same polysiloxane same ((CF4 "CF.sub.4") same (N2 "N. sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 06:01
S248	12	etch$4 same polysiloxane and ((CF4 "CF.sub.4") same (N2 "N. sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 06:04
S249	6	S248 not S247	US-PGPUB; USPAT	OR	ON	2007/10/10 06:01
S250	40	etch$4 same polysiloxane and ((CF4 "CF.sub.4") and (N2 "N. sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 06:09
S251	28	S250 not S248	US-PGPUB; USPAT	OR	ON	2007/10/10 06:04
S252	174	etch$4 and polysiloxane and ((CF4 "CF.sub.4") and (N2 "N. sub.2" nitrogen)) not S250	US-PGPUB; USPAT	OR	ON	2007/10/10 06:10

S253	44	etch$4 and polysiloxane and ((CF4 "CF.sub.4") same (N2 "N. sub.2" nitrogen)) not S250	US-PGPUB; USPAT	OR	ON	2007/10/10 06:31
S254	20	etch$4 and polysiloxane and ((CF4 "CF.sub.4") with (N2 "N. sub.2" nitrogen)) not S250	US-PGPUB; USPAT	OR	ON	2007/10/10 06:22
S255	24	S253 not S254	US-PGPUB; USPAT	OR	ON	2007/10/10 06:22
S256	0	etch$4 and polysiloxane same ((CF4 "CF.sub.4") and (N2 "N. sub.2" nitrogen) not S250	US-PGPUB; USPAT	OR	ON	2007/10/10 06:31
S257	6	etch$4 and polysiloxane same ((CF4 "CF.sub.4") and (N2 "N. sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 06:31
S258	310	etch$4 same (C4F8 "C.sub.4 F. sub.8") same (N2 "N.sub.2" nitrogen)	US-PGPUB; USPAT	OR	ON	2007/10/10 08:26
S259	183	etch$4 same (C4F8 "C.sub.4 F. sub.8") with (N2 "N.sub.2" nitrogen)	US-PGPUB; USPAT	OR	ON	2007/10/10 08:26
S260	145	etch$4 with (C4F8 "C.sub.4 F. sub.8") with (N2 "N.sub.2" nitrogen)	US-PGPUB; USPAT	OR	ON	2007/10/10 08:26
S261	27	etch$4 with (C4F8 "C.sub.4 F. sub.8") with (N2 "N.sub.2" nitrogen) same ratio	US-PGPUB; USPAT	OR	ON	2007/10/10 08:26

S262	46	etch$4 with (O-BARC O-BARL org-BARC org-BARL BCB O-SOG organic) with ((CF4 "CF.sub.4") with (N2 "N.sub.2" nitrogen))	US-PGPUB; USPAT	OR	ON	2007/10/10 09:36
S263	1	(US-6355572-$).did.	USPAT	OR	ON	2007/10/10 09:52
S264	1	S263 and (ar argon)	USPAT	OR	ON	2007/10/10 09:53
S265	1	S263	USPAT	OR	ON	2007/10/10 11:24
S266	7	"5262358" | "5721156" | "5835987" | "6410437" | "6455411" | "6506680" | "6570257").PN.	USPAT	OR	ON	2007/10/10 11:30
S267	24	(US-20020195419-$ or US-20020074309-$ or US-20010027016-$).did. or (US-6245489-$ or US-5604380-$ or US-6340435-$ or US-6281135-$ or US-6255180-$ or US-5658425-$ or US-5173151-$ or US-5522957-$ or US-6235453-$ or US-6168726-$ or US-6472317-$ or US-6417090-$ or US-6331380-$ or US-5721156-$ or US-6153514-$ or US-5835987-$ or US-6461962-$ or US-6051153-$ or US-5605600-$ or US-6376386-$ or US-6617253-$).did.	US-PGPUB; USPAT	OR	ON	2007/10/10 11:25

S268	10	(US-20050090634-$).did. or (US-6325861-$ or US-6143665-$ or US-6136211-$ or US-6060400-$ or US-6355567-$ or US-4976818-$).did. or (WO-9933096-$).did. or (JP-11145114-$).did. or (US-5854119-$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/10/10 11:25
S269	33	(US-20020058362-$).did. or (US-6284149-$ or US-6143665-$ or US-6060400-$ or US-6326307-$ or US-6440864-$ or US-6221745-$ or US-5801094-$ or US-6720249-$ or US-6342449-$ or US-6319815-$ or US-6211035-$ or US-6177329-$ or US-6284642-$ or US-6180975-$ or US-5204276-$ or US-6015751-$ or US-6737350-$ or US-6573196-$ or US-6180518-$ or US-6033979-$ or US-6014979-$ or US-5972789-$ or US-5654233-$ or US-6455411-$ or US-6472717-$ or US-6040223-$).did. or (US-6211051-$ or US-6163407-$ or US-6159661-$ or US-5990015-$ or US-5038713-$).did. or (JP-11145114-$).did.	US-PGPUB; USPAT; JPO	OR	ON	2007/10/10 11:25
S270	4	(US-6326307-$ or US-6455411-$ or US-6872665-$ or US-6686296-$).did.	USPAT	OR	ON	2007/10/10 11:26

S271	16	(US-20010010970-$ or US-20010009803-$ or US-20060166485-$).did. or (US-6211061-$ or US-6168726-$ or US-6309962-$ or US-6143665-$ or US-6107155-$ or US-6319815-$ or US-6909190-$ or US-6316160-$ or US-7060605-$ or US-6570257-$ or US-6410437-$ or US-6316351-$ or US-6475918-$).did.	US-PGPUB; USPAT	OR	ON	2007/10/10 11:26
S272	11	(US-20010010970-$).did. or (US-6211061-$ or US-6168726-$ or US-6309962-$ or US-6143665-$ or US-6107155-$ or US-6319815-$ or US-6316160-$ or US-6570257-$ or US-6410437-$ or US-6475918-$).did.	US-PGPUB; USPAT	OR	ON	2007/10/10 11:26
S273	16	(US-20060231525-$ or US-20040050816-$ or US-20030222048-$ or US-20050079717-$ or US-20040092111-$ or US-20020094695-$).did. or (US-7097781-$ or US-7090784-$ or US-6565763-$ or US-6805139-$ or US-6570257-$ or US-6316351-$ or US-6284642-$ or US-6284149-$ or US-6355572-$ or US-6013547-$).did.	US-PGPUB; USPAT	OR	ON	2007/10/10 11:26

S274	88	S267 S268 S269 S270 S271 S272 S273	US-PGPUB; USPAT	OR	ON	2007/10/10 11:26
S275	83	S274 not S266	US-PGPUB; USPAT	OR	ON	2007/10/10 11:27
S276	0	polysiloxane adj TEOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 18:34
S277	0	polysiloxane near TEOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 18:34
S278	58	polysiloxane with TEOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/29 18:35
S279	2	"6251770".PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/29 19:19
S280	28	dielectric adj constant near TEOS	US-PGPUB; USPAT	OR	ON	2008/03/29 19:58
S281	1	"7419902".PN.	USPAT	OR	OFF	2009/02/03 10:55
S282	1	S281 and (CF4 "CF.sub.4")	US-PGPUB; USPAT	OR	ON	2009/02/03 11:01

S283	0	10-265526	JPO; DERWENT	OR	ON	2009/02/03 11:03
S284	35	"265526"	JPO; DERWENT	OR	ON	2009/02/03 11:03
S285	2	S284 and toshiba	JPO; DERWENT	OR	ON	2009/02/03 11:03
S286	4	"2001068455"	JPO; DERWENT	OR	ON	2009/02/03 11:04
S287	1	2001-278484.NRAN.	DERWENT	OR	ON	2009/02/03 11:07
S288	2	"10265526"	JPO; DERWENT	OR	ON	2009/02/03 11:11
S289	1	1998-589740.NRAN.	DERWENT	OR	ON	2009/02/03 11:11
S290	2	(("5658425") or ("6284149")). PN.	USPAT	OR	OFF	2009/02/04 15:03
S291	3687	(n2 "n.sub.2" nitrogen adj gas). drwd.	US-PGPUB; USPAT	OR	ON	2009/04/14 16:31
S292	74579	rate$4.drwd.	US-PGPUB; USPAT	OR	ON	2009/04/14 16:31
S293	851	S291 and S292	US-PGPUB; USPAT	OR	ON	2009/04/14 16:31
S294	183	S293 and ("216"/$.ccls. "438"/$. ccls.)	US-PGPUB; USPAT	OR	ON	2009/04/14 16:32
S295	66	S294 and @ad<"19991026"	US-PGPUB; USPAT	OR	ON	2009/04/14 16:33
S296	21	S295 and (CF4 "CF.sub.4")	US-PGPUB; USPAT	OR	ON	2009/04/14 16:33

S297	6	S296 and (CF4 "CF.sub.4") with (n2 "n.sub.2" nitrogen adj gas)	US-PGPUB; USPAT	OR	ON	2009/04/14 16:34
S298	3	S295 and tetrafluoride not S297	US-PGPUB; USPAT	OR	ON	2009/04/14 16:38
S299	1	S295 and tetrafluoride not S296	US-PGPUB; USPAT	OR	ON	2009/04/14 16:38
S300	1	S295 and (fluorcarbon hydrofluorocarbon) not S296	US-PGPUB; USPAT	OR	ON	2009/04/14 16:41
S301	846	(CF4 "CF.sub.4") with (N2 "N. sub.2") with (Ar argon) same etch$4	US-PGPUB; USPAT	OR	ON	2009/06/19 14:02
S302	156	(CF4 "CF.sub.4") near2 (N2 "N. sub.2") near2 (Ar argon) same etch$4	US-PGPUB; USPAT	OR	ON	2009/06/19 14:03
S303	54	(CF4 "CF.sub.4") near (N2 "N. sub.2") near (Ar argon) same etch$4	US-PGPUB; USPAT	OR	ON	2009/06/19 14:03
S304	41	(CF4 "CF.sub.4") near (N2 "N. sub.2") near (Ar argon) WITH etch$4	US-PGPUB; USPAT	OR	ON	2009/06/19 14:03

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